EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S322	6	S321 and ((((different or higher or lower or greater) near3 threshold) with thickness)	US-PGPUB; USPAT	OR	ON	2006/04/17 11:49
S215	7	S214 not S213	US-PGPUB; USPAT	OR	ON	2006/04/17 11:49
S325	8	S324 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2006/04/17 11:50
S324	9	S323 not S322	US-PGPUB; USPAT	OR	ON	2006/04/17 11:51
S327	23	S326 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2006/04/17 11:55
S326	25	fin$1fet and ((gate adj (dielectric or insulator or insulating or insulation)) with (thickness near different))	US-PGPUB; USPAT	OR	ON	2006/04/17 11:55
S269	21	S268 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2006/04/17 11:55
S328	22	S327 not S323	US-PGPUB; USPAT	OR	ON	2006/04/17 11:56
S309	0	S308 not (S305 or S301 or S285 or S281 or S277 or S272 or S269 or S270)	US-PGPUB; USPAT	OR	ON	2006/04/17 12:18
S323	10	S321 and ((gate adj (dielectric or insulator or insulating or insulation)) with (thicker))	US-PGPUB; USPAT	OR	ON	2006/04/25 15:56
S331	0	(((each or individual) adj fin) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	US-PGPUB; USPAT	OR	ON	2006/04/25 15:57
S333	0	(((each or individual) adj fin) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) with (thickness))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 15:58
S334	8	(fin with (gate adj (dielectric or insulator or insulating or insulation or oxide)) with (thickness))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 15:59
S330	0	(((each or individual) adj fin) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) with (thickness))	US-PGPUB; USPAT	OR	ON	2006/04/25 16:02
S332	1	((different adj fin) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	US-PGPUB; USPAT	OR	ON	2006/04/25 16:03
S339	4	S338 and (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))	US-PGPUB; USPAT	OR	ON	2006/04/25 16:05
S341	3	S340 and (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 16:06
S345	0	S344 not S343	US-PGPUB; USPAT	OR	ON	2006/04/25 16:09
S344	2	((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S342	US-PGPUB; USPAT	OR	ON	2006/04/25 16:09
S343	2	((different adj thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S342	US-PGPUB; USPAT	OR	ON	2006/04/25 16:24
S346	2	((different near2 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S342	US-PGPUB; USPAT	OR	ON	2006/04/25 16:25
S350	0	S349 not S343	US-PGPUB; USPAT	OR	ON	2006/04/25 16:26
S349	2	((different near3 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S348	US-PGPUB; USPAT	OR	ON	2006/04/25 16:26

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S34 7	2	((different near3 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S342	US-PGPUB; USPAT	OR	ON	2006/04/25 16:26
S35 2	3	(((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top)) and S348	US-PGPUB; USPAT	OR	ON	2006/04/25 16:31
S35 1	3	((different near3 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top)) and S348	US-PGPUB; USPAT	OR	ON	2006/04/25 16:31
S35 8	0	S357 not S352	US-PGPUB; USPAT	OR	ON	2006/04/25 16:32
S35 6	0	S354 not S352	US-PGPUB; USPAT	OR	ON	2006/04/25 16:32
S35 7	3	(((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top)) and S353	US-PGPUB; USPAT	OR	ON	2006/04/25 17:19
S36 1	0	((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S359	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 17:21
S36 0	0	(((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top)) and S359	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 17:21
S36 3	8	(((multi or multiple) adj (channel)) with ((fin adj fet) or fin$1fet))	US-PGPUB; USPAT	OR	ON	2006/04/25 17:27
S36 2	7	(multi$1finfet or ((multi or multiple) adj ((fin adj fet) or fin$1fet)) or multiple$1finfet)	US-PGPUB; USPAT	OR	ON	2006/04/25 17:27
S36 6	0	(different with thickness with (gate adj (dielectric or insulator or insulating or insulation or oxide))) and S364	US-PGPUB; USPAT	OR	ON	2006/04/25 17:28
S36 5	33	(different with thickness with (gate adj (dielectric or insulator or insulating or insulation or oxide))) and S337	US-PGPUB; USPAT	OR	ON	2006/04/25 17:28
S35 4	3	((different near3 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top)) and S353	US-PGPUB; USPAT	OR	ON	2006/04/25 17:28
S36 7	1	((multiple$1channel or ((several) adj (channel)) or multi$1channel) with ((fin adj fet) or fin$1fet))	US-PGPUB; USPAT	OR	ON	2006/04/25 17:29
S36 4	8	((multiple$1channel or ((multi or multiple) adj (channel)) or multi$1channel) with ((fin adj fet) or fin$1fet))	US-PGPUB; USPAT	OR	ON	2006/04/25 17:29
S33 7	33	S336 and (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))	US-PGPUB; USPAT	OR	ON	2006/04/26 17:43
S36 9	9	(fins with (thicknesses or thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	US-PGPUB; USPAT	OR	OFF	2006/04/26 17:49
S37 2	18	S371 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2006/04/26 17:50
S37 1	20	S370 not S369	US-PGPUB; USPAT	OR	ON	2006/04/26 17:50
S37 4	4	S373 not S372	US-PGPUB; USPAT	OR	ON	2006/04/26 17:55
S37 3	4	(fin with (thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top)	US-PGPUB; USPAT	OR	ON	2006/04/26 17:55
S37 6	2	(fin with ((thicknesses or thickness) near different) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 17:56

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S37 0	23	(fin with ((thicknesses or thickness) near different) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	US-PGPUB; USPAT	OR	ON	2006/04/26 17:56
S37 7	2	((fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) with ((thicknesses or thickness) near different) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 17:57
S37 8	4	((fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) with ((thicknesses or thickness) near different) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	US-PGPUB; USPAT	OR	ON	2006/04/26 17:58
S38 1	0	S379 and ((thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top)	US-PGPUB; USPAT	OR	ON	2006/04/26 17:59
S38 0	0	S379 and ((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top)	US-PGPUB; USPAT	OR	ON	2006/04/26 17:59
S37 5	0	(fin with (thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 17:59
S37 9	14	((fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) with (array or cell) with (periphery or peripheral))	US-PGPUB; USPAT	OR	ON	2006/04/26 18:09
S38 2	7	((fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) with ((different or higher or lower) near2 threshold))	US-PGPUB; USPAT	OR	ON	2006/04/26 18:15
S38 4	3	((fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) with ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide))))	US-PGPUB; USPAT	OR	ON	2006/04/26 18:16
S38 5	2	((fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) with ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide))))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 18:19
S38 8	1	(fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) and ((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 18:20
S38 7	0	(fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) and ((thicker or thinner) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 18:20
S38 6	2	(fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet))) and ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 18:21
S38 9	0	(("2nd" or second or several or many or "plurality") adj (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))) and ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 18:22
S39 2	12	(("2nd" or second or several or many or "plurality") adj (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))) and ((different or higher or lower) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))	US-PGPUB; USPAT	OR	ON	2006/04/26 18:23
S39 1	0	(("2nd" or second or several or many or "plurality") adj (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))) and ((different or higher or lower) near3 (gate adj (dielectric or insulator or insulating or insulation or oxide)))	US-PGPUB; USPAT	OR	ON	2006/04/26 18:23

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S39 0	0	(("2nd" or second or several or many or "plurality") adj (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))) and ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide)))	US-PGPUB; USPAT	OR	ON	2006/04/26 18:23
S39 6	4	S395 and ((gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thicker or thinner))	US-PGPUB; USPAT	OR	ON	2006/04/30 12:44
S36 8	3	(several adj fin) and (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))	US-PGPUB; USPAT	OR	ON	2006/04/30 12:55
S39 9	24	(silicide with (capping or cap)) and (fin$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)))	US-PGPUB; USPAT	OR	ON	2006/04/30 12:56